

BRD4N50F

Rev.A Apr.-2024



蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

TO-252 N MOS

N-CHANNEL MOSFET in a TO-252 Plastic Package.

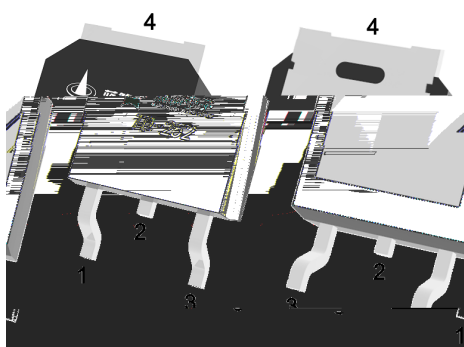
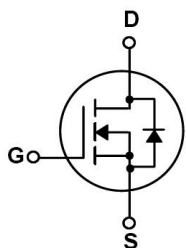
$V_{DS}=500V$ $I_D=4A$

$R_{DS(ON)}@10V$ 2.2 Ω (Typ. 1.7 Ω)

Fast Switching.

HF Product.

These devices are well suited for power switch circuit of adaptor and charger, intergrate fast recovery diode.



PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	500	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	4	A
Drain Current - Pulsed	I_{DM}	8	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	176.4	mJ
Avalanche Current	I_{AS}	6.3	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	50	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	
Junction to Ambient	R_{JA}	110	/W
Junction to Case	R_{JC}	2.5	/W

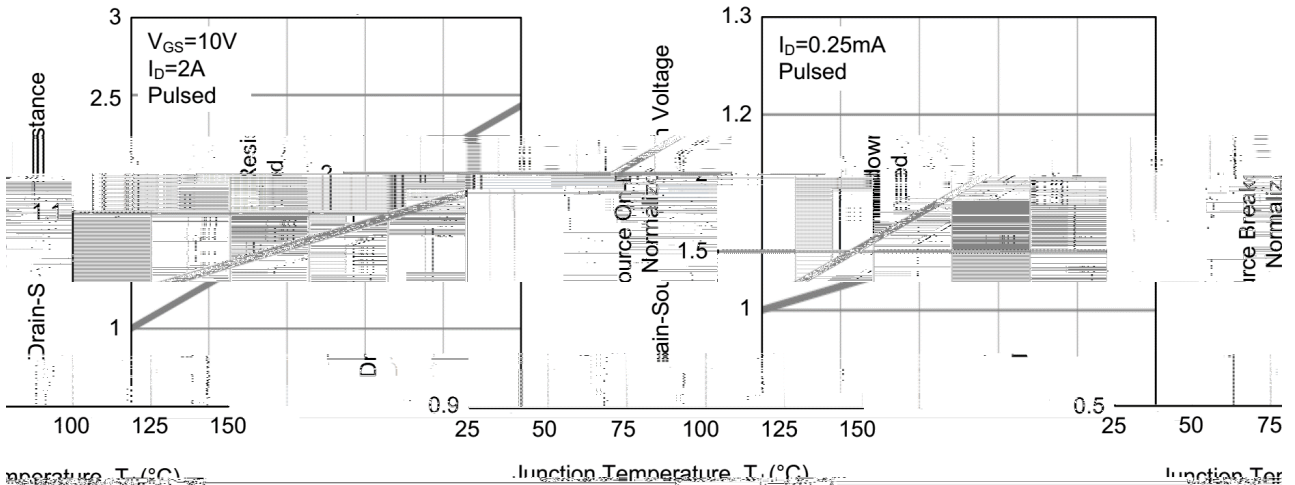
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	500			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=500V$ $V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A$		1.7	2.2	Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		350		pF
Output Capacitance	C_{oss}			145		
Reverse Transfer Capacitance	C_{rss}			5		
Total Gate Charge	Q_G	$V_{DS}=400V$ $I_D=4.0A$ $V_{GS}=10V$		8.5		nC
Gate-Source Charge	Q_{GS}			3.2		
Gate-Drain Charge	Q_{GD}			1.5		

/ **Electrical Characteristics**(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=100V$ $I_D=4.0A$ $V_{GS}=10V$ $R_G=25\Omega$		4.3		ns
Turn-On Rise Time	t_r			17.2		
Turn-Off Delay Time	$t_{d(off)}$			22		
Turn-Off Fall Time	t_f			23.2		
Maximum Continuous Drain-Source Diode Forward Current	I_S				4	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				8	A
Reverse Recovery Time	t_{rr}	$V_{GS}=0V$ $I_S=5.0A$ $dI_F/dt=100 A/\mu s$		92		ns
Reverse Recovery Charge	Q_{rr}			1.45		μC

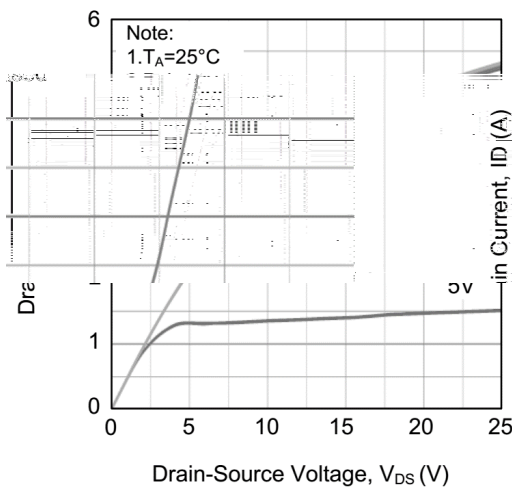
/ Electrical Characteristic Curve



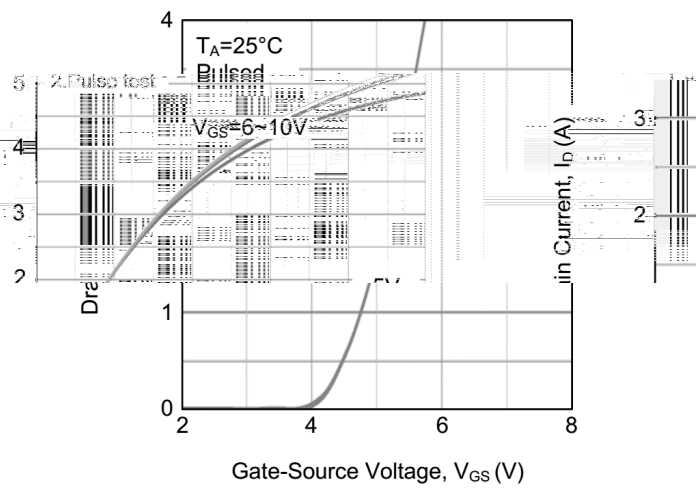
1. Drain-Source On-Resistance vs. Junction Temperature

2. Breakdown Voltage vs. Junction Temperature

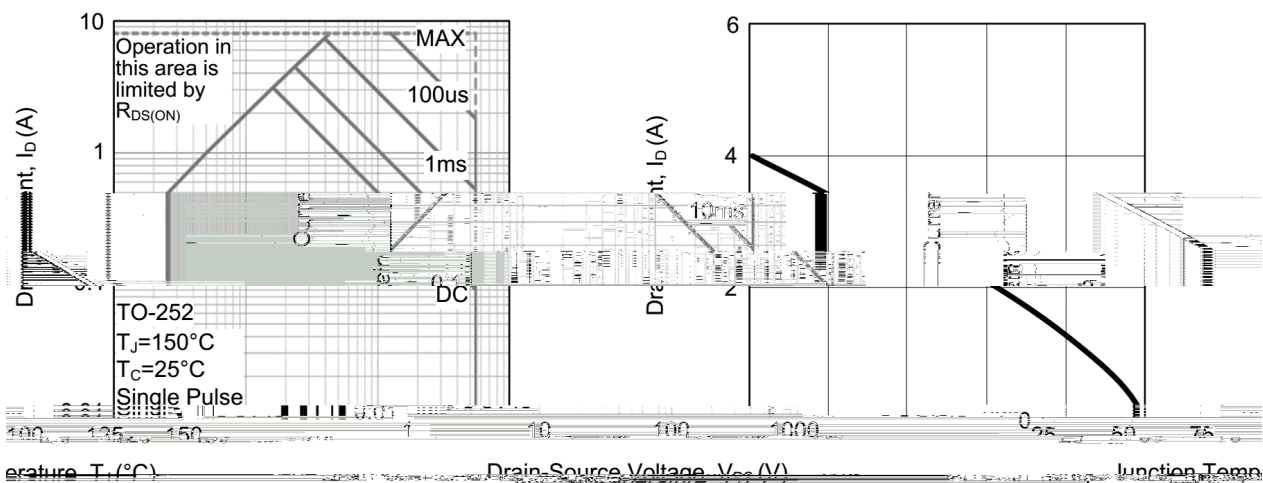
1. Drain-Source On-Resistance vs. Junction Temperature



3. Drain Current vs. Drain-Source Voltage



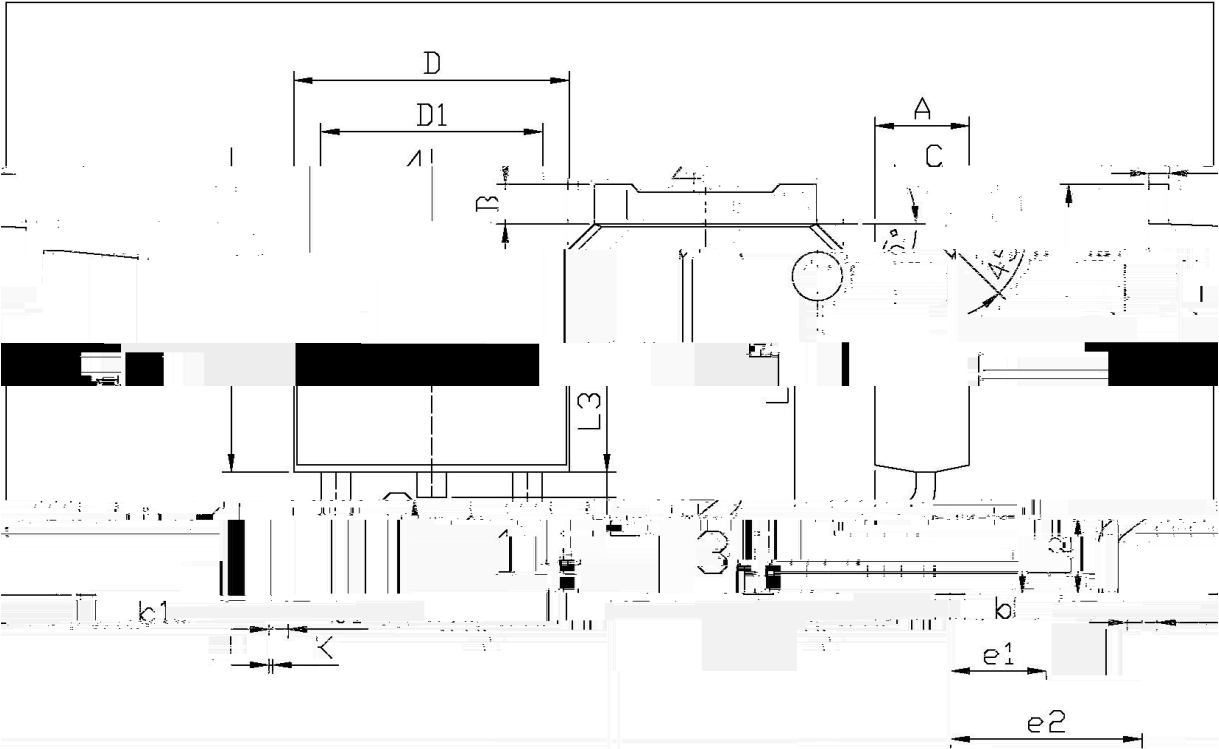
4. Drain Current vs. Gate-Source Voltage



5. Safe Operating Area

6. Drain Current vs. Junction Temperature

/ Package Dimensions

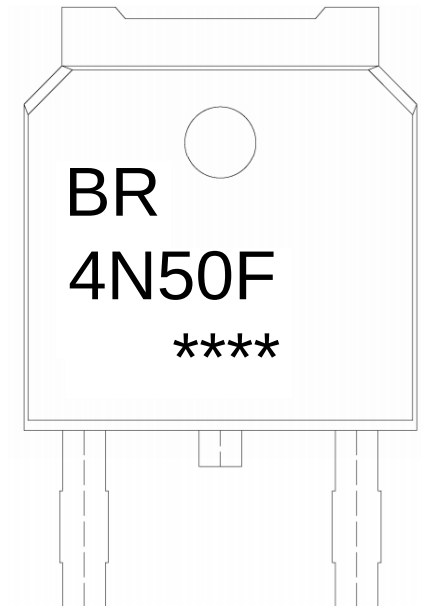


单位: mm

Symbol		Dimensions In Millimeters		Symbol		Dimensions In Millimeters	
		Min	Max			Min	Max
A		5.05	6.25	e1		2.24	2.34
B1		0.95	1.25	L3		9.85	10.35
C		0.45	0.55	D		6.45	6.75
D1		5.10	5.50	e2		0.60	0.90

TO-252

/ **Marking Instructions**



BR

Note:

BR: Company Code

4N50F: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 盒/箱	Reel	Inner Box 盒	Outer Box 箱

TO-252 2,elInne576J/TT1lsLA01A5V)Ba5a@7121L82560E7SCM55MC6HXcmH5Y4(Cd2dgh5Y4P826H5Y4P8ECM0%8Htc